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Appl. No. 10/069,031
Amdt. dated September , 2006
Reply to Office Action of 08/16/2006

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AMENDMENTS TO THE CLAIMS

Original claims 1-39 were canceled and new claims 40-66 were presented therefor in the Preliminary Amendment filed July 5, 2002.

Please amend claims 40 and 46 as set forth in the following listing of the claims.

Claims 1-39 (canceled)

40. (currently amended) A method for the deposition of semiconductor layers comprising SiC and/or $\text{SiC}_x\text{Ge}_{1-x}$ ($0 < x < 1$), AlN, GaN by a CVD method, wherein:

at least one substrate is located within and is heated by an actively heated flow channel reactor to a temperature of approximately 1100°C to approximately 1800°C;

the at least one substrate rotates in the actively heated flow channel reactor, and the heating by the reactor is accomplished by an elevated temperature of heated